

MBRM110ET1G, NRVBM110ET1G

Schottky Power Rectifier, Surface Mount, 1.0 A, 10 V

The Schottky POWERMITE[®] employs the Schottky Barrier principle with a barrier metal and epitaxial construction that produces optimal forward voltage drop–reverse current tradeoff. The advanced packaging techniques provide for a highly efficient micro miniature, space saving surface mount Rectifier. With its unique heatsink design, the POWERMITE[®] has the same thermal performance as the SMA while being 50% smaller in footprint area, and delivering one of the lowest height profiles, < 1.1 mm in the industry. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC–DC and DC –DC converters, reverse battery protection, and “ORing” of multiple supply voltages and any other application where performance and size are critical.

Features

- Low I_R Extends Battery Life
- Low Profile – Maximum Height of 1.1 mm
- Small Footprint – Footprint Area of 8.45 mm²
- 150°C Operating Junction Temperature
- Low Thermal Resistance with Direct Thermal Path of Die on Exposed Cathode Heat Sink
- ESD Ratings:
 - ◆ Human Body Model = 3B (> 16 kV)
 - ◆ Machine Model = V (> 400 V)
- AEC–Q101 Qualified and PPAP Capable
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- All Packages are Pb–Free*

Mechanical Characteristics:

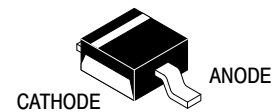
- POWERMITE[®] is JEDEC Registered as D0–216AA
- Case: Molded Epoxy
- Epoxy Meets UL 94 V–0 @ 0.125 in
- Weight: 16.3 mg (Approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Maximum for 10 Seconds



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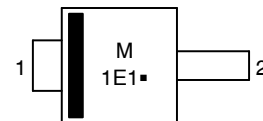
<http://onsemi.com>

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES, 10 VOLTS



POWERMITE
CASE 457
PLASTIC

MARKING DIAGRAM



M = Date Code
1E1 = Device Code
▪ = Pb–Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRM110ET1G	POWERMITE (Pb–Free)	3,000 / Tape & Reel
NRVBM110ET1G	POWERMITE (Pb–Free)	3,000 / Tape & Reel
MBRM110ET3G	POWERMITE (Pb–Free)	12,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	10	V
Average Rectified Forward Current ($T_L = 100^\circ\text{C}$)	I_O	1.0	A
Non-Repetitive Peak Surge Current (Non-Repetitive peak surge current, halfwave, single phase, 60 Hz)	I_{FSM}	50	A
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	-55 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R , $T_J = 25^\circ\text{C}$)	dv/dt	10,000	V/ μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Anode) (Note 1)	R_{tjl}	35	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Tab (Cathode) (Note 1)	R_{tjtab}	23	
Thermal Resistance, Junction-to-Ambient (Note 1)	R_{tja}	277	

1. Mounted with minimum recommended pad size, PC Board FR4, See Figures 8 and 9.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value		Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 0.1\text{ A}$) ($I_F = 1.0\text{ A}$) ($I_F = 2.0\text{ A}$)	V_F	$T_J = 25^\circ\text{C}$	$T_J = 100^\circ\text{C}$	V
	V_F	0.455 0.530 0.595	0.360 0.455 0.540	V
Maximum Instantaneous Reverse Current (Note 2) ($V_R = 5.0\text{ V}$) ($V_R = 10\text{ V}$)	I_R	$T_J = 25^\circ\text{C}$	$T_J = 100^\circ\text{C}$	μA
		0.5 1.0	300 500	

2. Pulse Test: Pulse Width $\leq 250\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

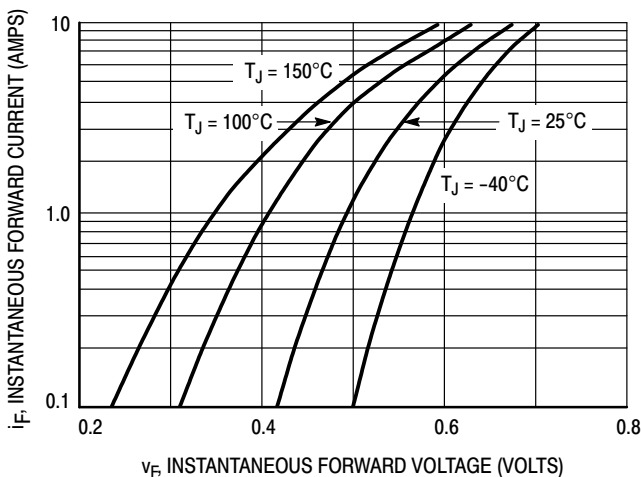


Figure 1. Typical Forward Voltage

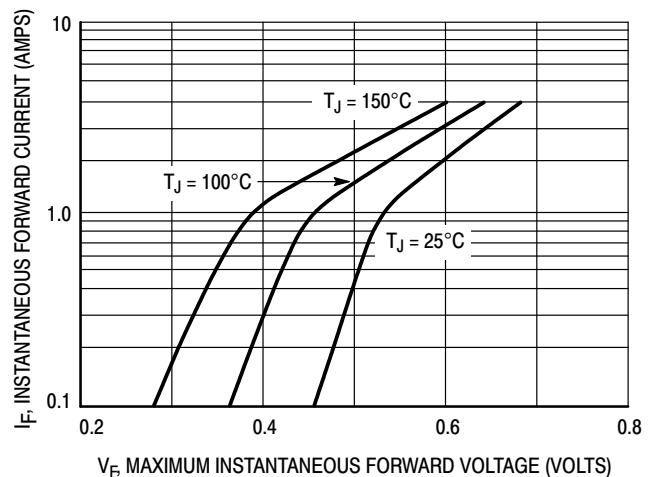


Figure 2. Maximum Forward Voltage

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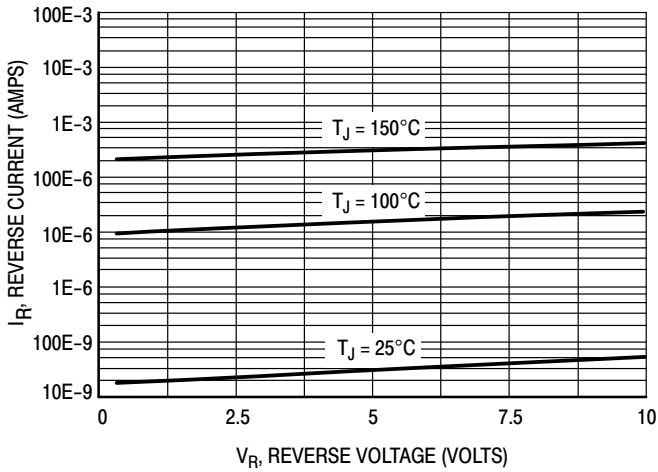


Figure 3. Typical Reverse Current

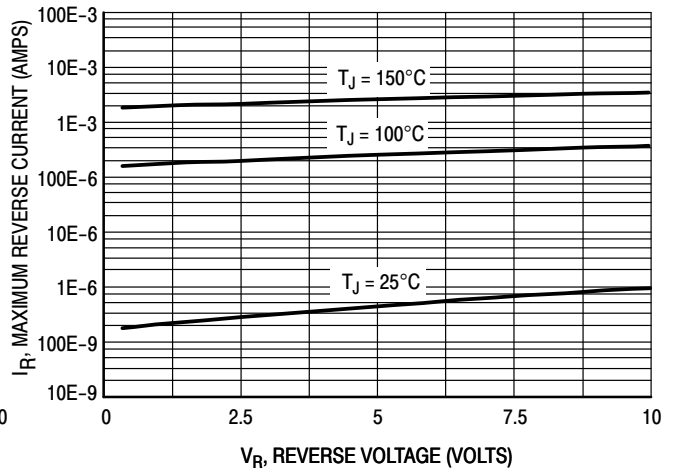


Figure 4. Maximum Reverse Current

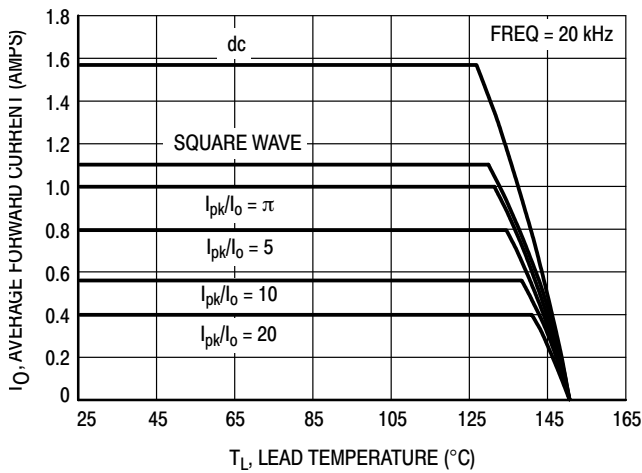


Figure 5. Current Derating

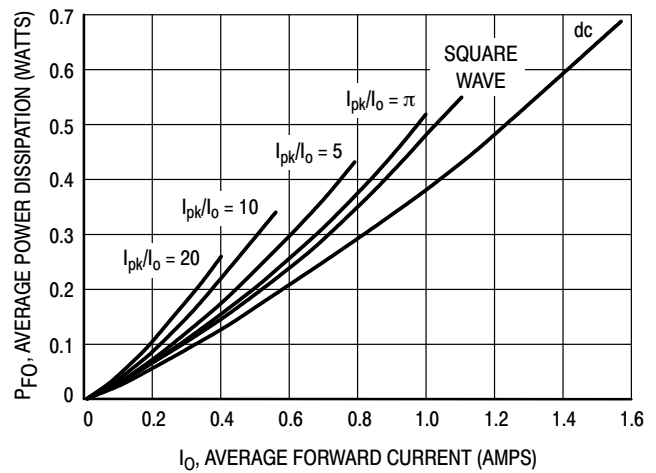


Figure 6. Forward Power Dissipation

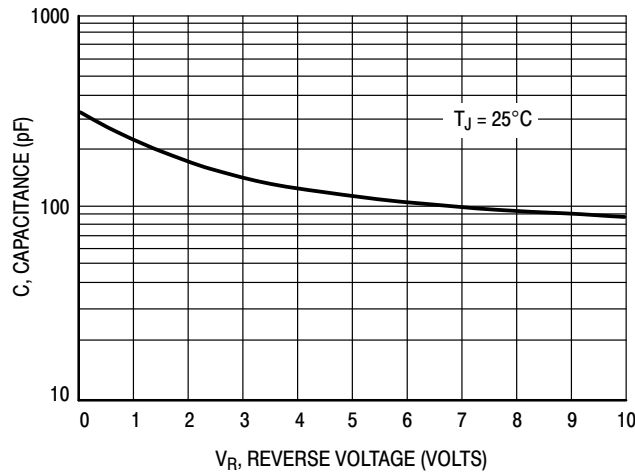


Figure 7. Capacitance

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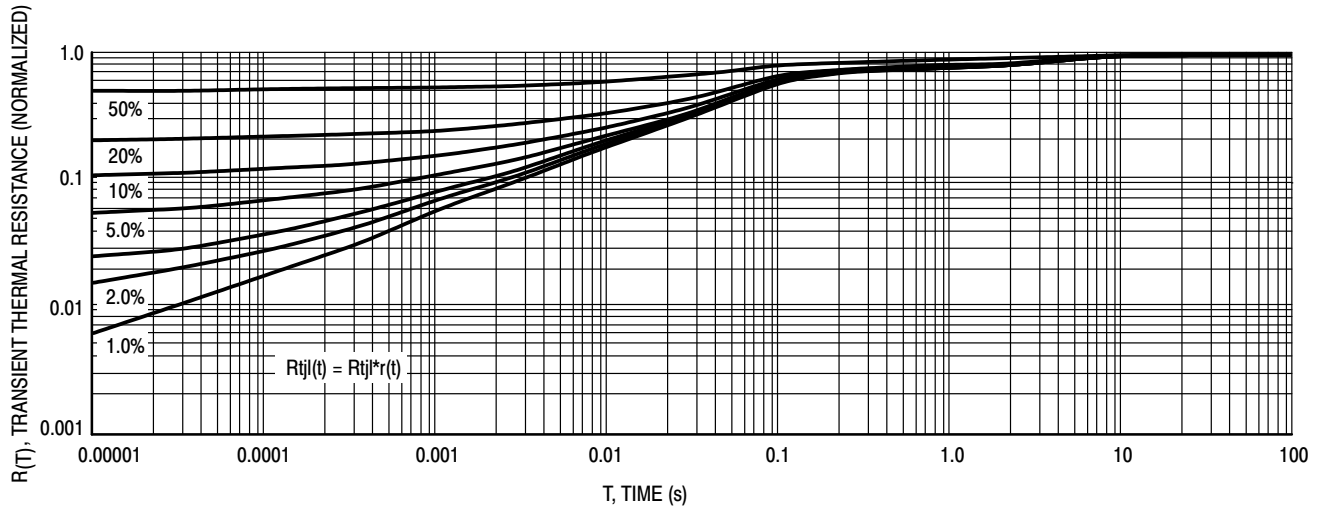


Figure 8. Thermal Response Junction to Lead

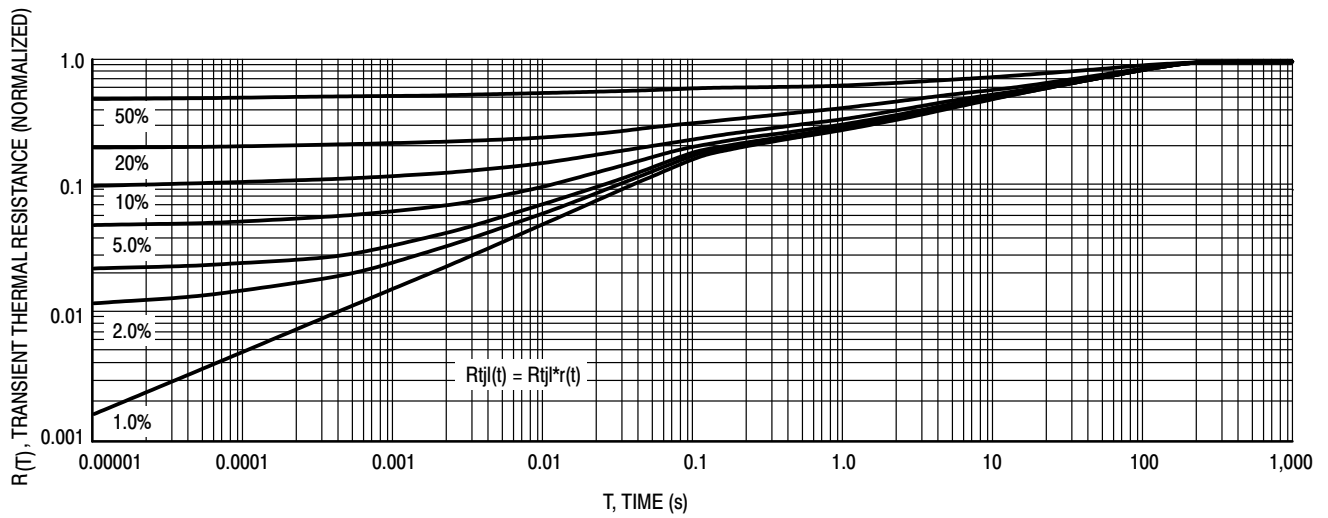
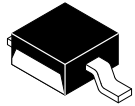


Figure 9. Thermal Response Junction to Ambient

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

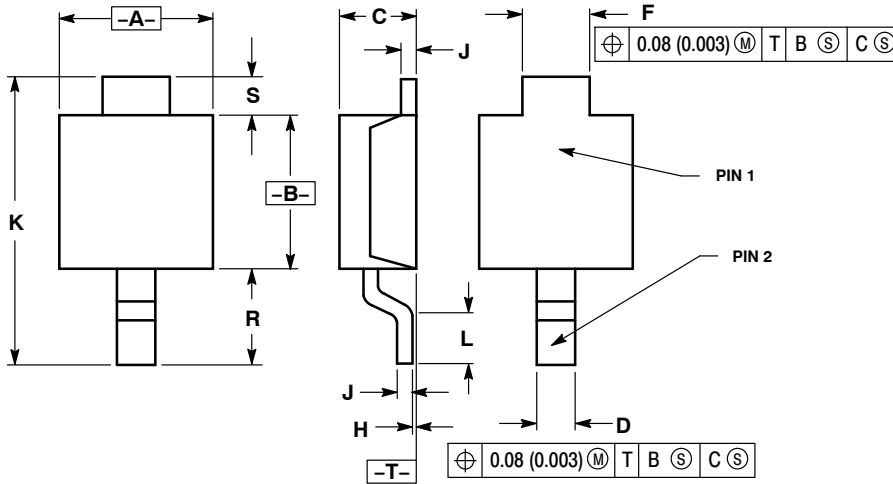
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SCALE 4:1

POWERMITE CASE 457-04 ISSUE F

DATE 14 MAY 2013



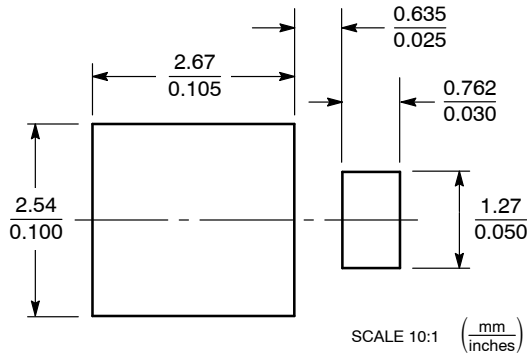
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

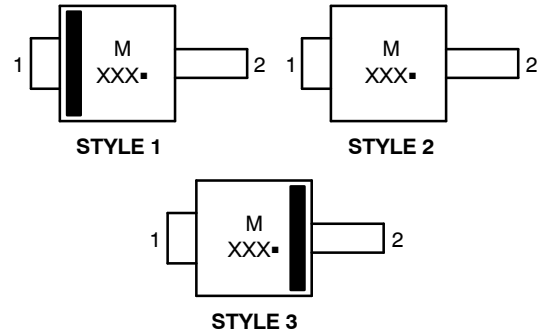
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.75	2.05	0.069	0.081
B	1.75	2.18	0.069	0.086
C	0.85	1.15	0.033	0.045
D	0.40	0.69	0.016	0.027
F	0.70	1.00	0.028	0.039
H	-0.05	+0.10	-0.002	+0.004
J	0.10	0.25	0.004	0.010
K	3.60	3.90	0.142	0.154
L	0.50	0.80	0.020	0.031
R	1.20	1.50	0.047	0.059
S	0.50	REF	0.019	REF

- STYLE 1:
PIN 1. CATHODE
2. ANODE
- STYLE 2:
PIN 1. ANODE OR CATHODE
2. CATHODE OR ANODE
(BI-DIRECTIONAL)
- STYLE 3:
PIN 1. ANODE
2. CATHODE

SOLDERING FOOTPRINT*



GENERIC MARKING DIAGRAMS*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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